Abstracts

A Wide-Band Push-Pull GaAs Monolithic Active Isolator

F. Ali and A. Podell. "A Wide-Band Push-Pull GaAs Monolithic Active Isolator." 1991 Microwave and Guided Wave Letters 1.2 (Feb. 1991 [MGWL]): 26-27.

A novel 2-6 GHz push-pull GaAs monolithic active isolator has been designed and tested. This balanced MESFET isolator has better than 18 db reverse isolation at 6 GHz and provides greater than 15 dB input and output return loss across the band. This small (actual chip area: 12 mils x 24 mils) isolator chip draws 20mA of current from a single +5V supply. The compact chip size makes it an ideal candidate for impedance matching for monolithic sub-systems where a ferrite isolator is not practical.

❑ Return to main document.